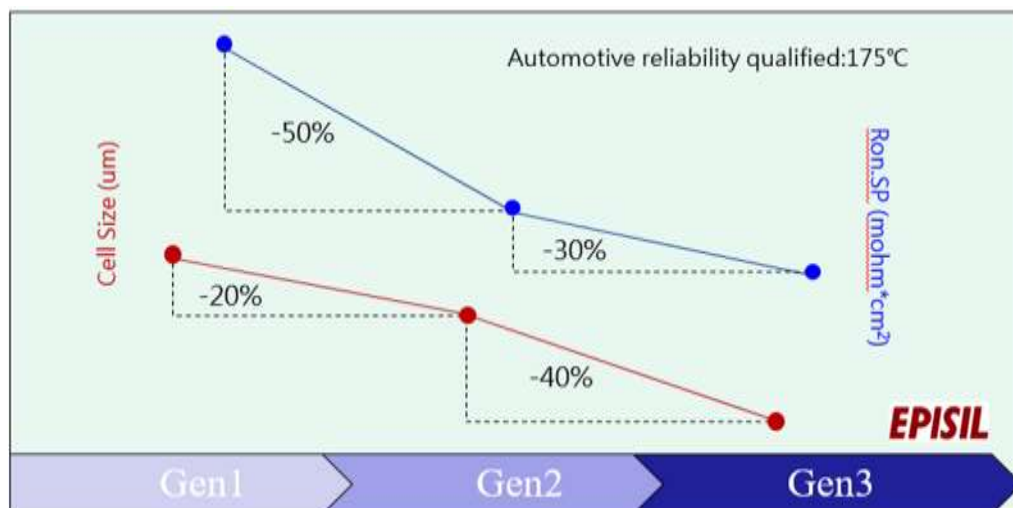


The Launch of Episil Third-Generation SiC Planar MOSFET Technology Platform

On July 1st 2024, Episil Technology officially launches the third generation (G3) of silicon carbide planar MOSFET. This new technology platform has passed the automotive scale reliability test of several customers on the client's 1200V products with over stress specification 1320V/175C junction temperature. Consequently, the chip size is reduced and $R_{ds(on)}$ is scaled down as well. Therefore, customers can effectively integrate power components with high efficiency. The platform provides customers with smaller, lower energy consumption and higher power density products, to meet the requirements of the most advanced market technology. Furthermore, the technology has been in parallel with the capabilities of international IDM manufacturers.



Episil R&D is consistently investing in new generation process technology. G3 SiC planar MOSFET technology platform is released officially to customers today. As above figure, the third generation reduces the cell area by about 40% and improves the on-resistance ($R_{on,SP}$) by 30% in above figure compared with the previous generation G2 platform. These fulfill customers' needs for both better efficiency and improved technology. At the same time, the technology opens more business opportunities for cooperation with international IDM customers.

Episil Technology has been deeply engaged in compound semiconductor technology and run in mass production for 10 years. Silicon carbide product technology specifically can be applied into the most advanced solar inverters, energy storage systems, cutting-edge EV vehicle modules, and is able to further support AI high-

performance computing power servers. Through the launch of a new generation of technology platforms, Episil facilitates customers in developing more competitive products. On the growth path of silicon carbide technology in various applications, Episil provides services that exceed the industry. At the same time, Episil will continue to develop next generation of process technology to meet customers' and markets' needs in developing more cutting-edge power supply designs, and is looking to become a leader in the pure-play compound semiconductor foundry industry.

About Episil Technology

Episil Technology (EPISIL, Taiwan Stock Exchange Code: 3707) was established in Taiwan's Hsinchu Science Park in 1985. It is the world's first pure-play bipolar integrated circuit (Linear Bipolar IC) foundry and the world's third pure-play compound semiconductors foundry available with both gallium nitride (GaN) and silicon carbide (SiC) technology. Currently it has one 4/5-inch and two 6-inch wafer fabs. For detailed information, please refer to the official website of Episil Technology: <https://www.episil.com>.